MULTIPLE EXPOSURE TECHNIQUE TO PATTERN TIGHT CONTACT GEOMETRIES

ABSTRACT OF THE DISCLOSURE

[0024] A mask pattern may be decomposed into two or more masks, each having a pitch greater than that of the original mask pattern. New, "partial-pattern" masks may be created for each of the new mask patterns. The original mask pattern is transferred to the photoresist for the corresponding layer using a multiple exposure technique in which the photoresist is exposed with each of the partial-pattern masks individually, e.g., back-to-back in a pass through a scanner, to define all of the features in the original pattern.